

FIG. 1C

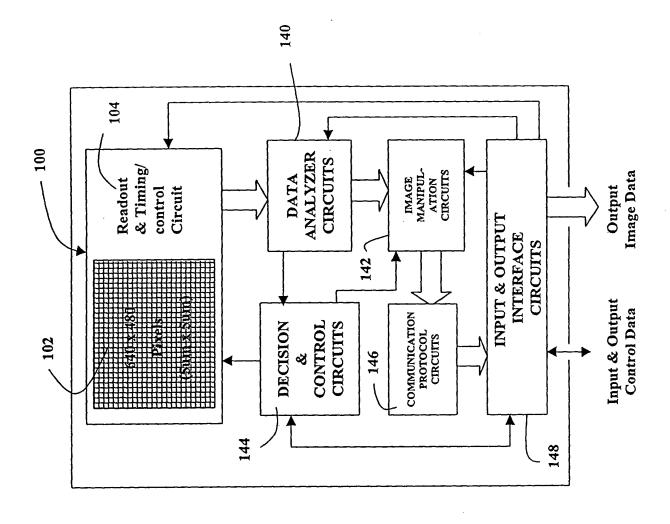
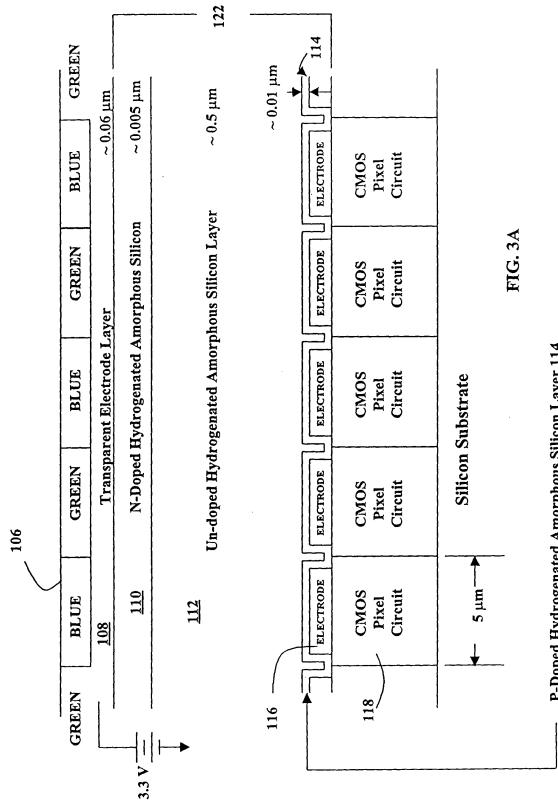
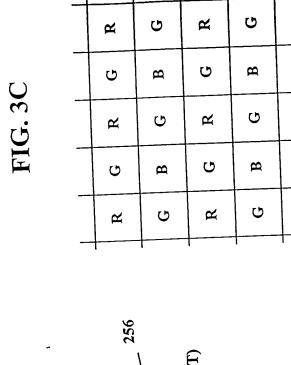


FIG.

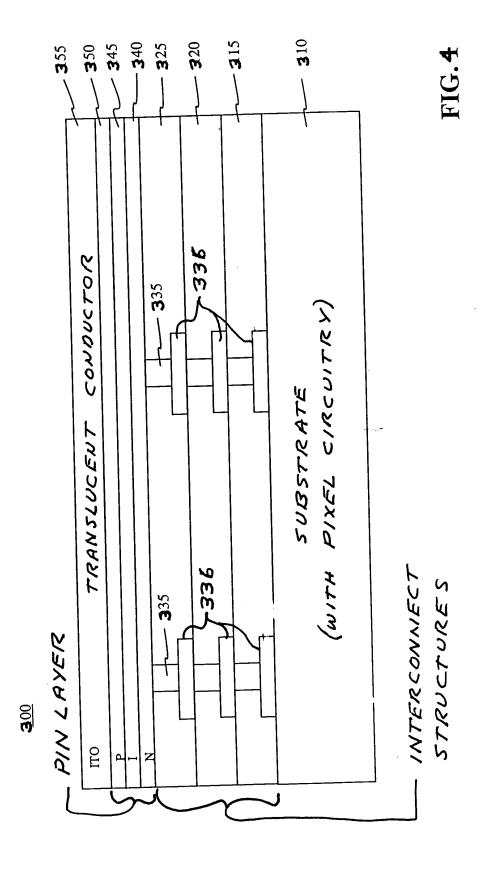


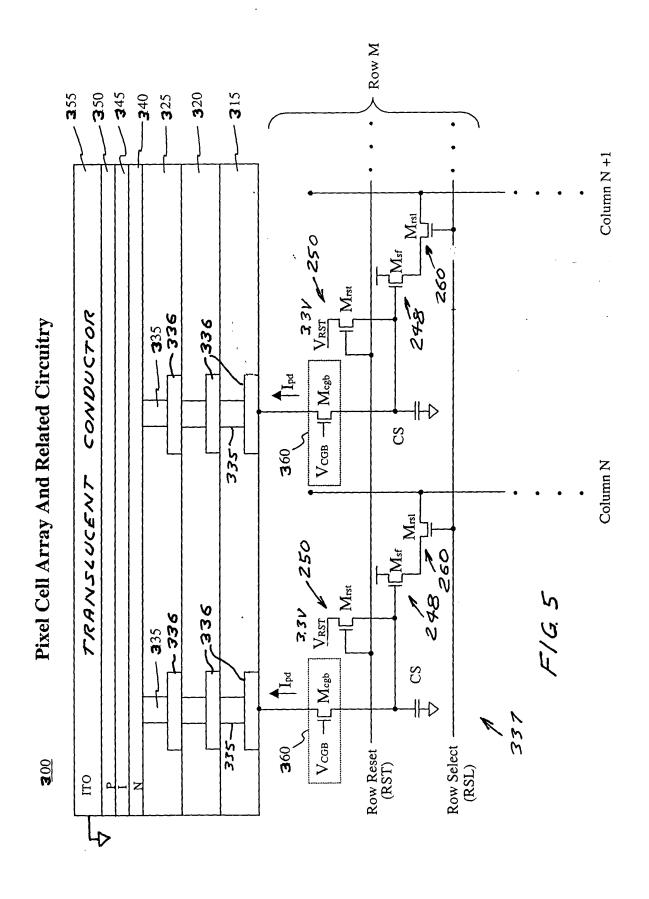
P-Doped Hydrogenated Amorphous Silicon Layer 114



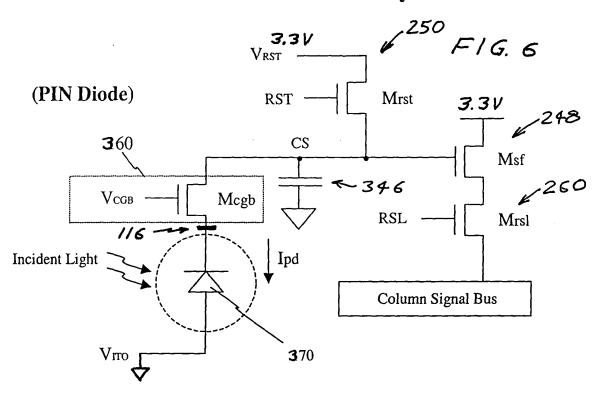
Vcc ~262 COL(OUT) 260 248 258 246 SEL L 118 Incident Light 122 CS = 120  $V_{\text{RST}}$ 250 108 116 -Ipd 252 RST

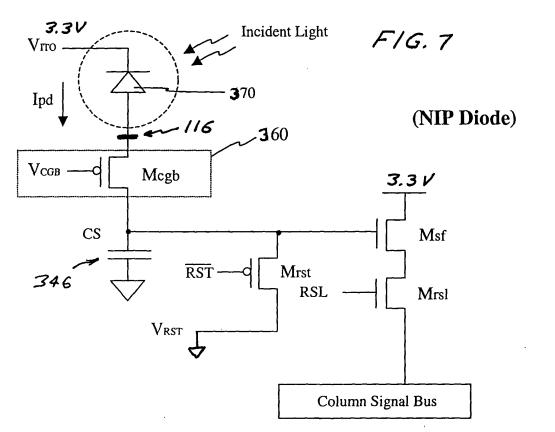
POAP Sensor Pixel Cell Array

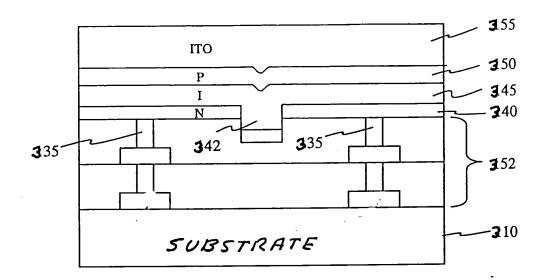




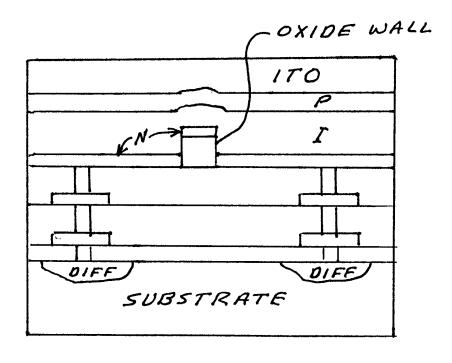
# **Individual Pixel Cell Circuitry**



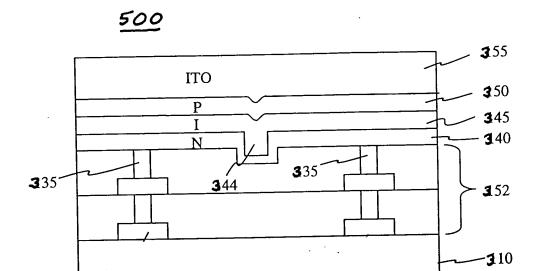




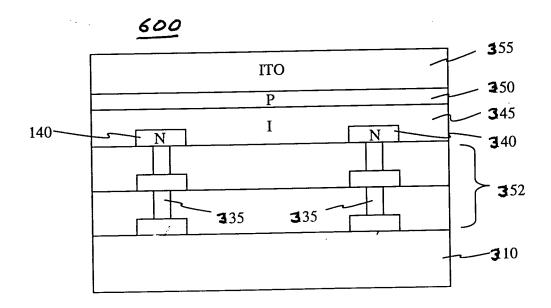
F/G. 8



F/G. 8A

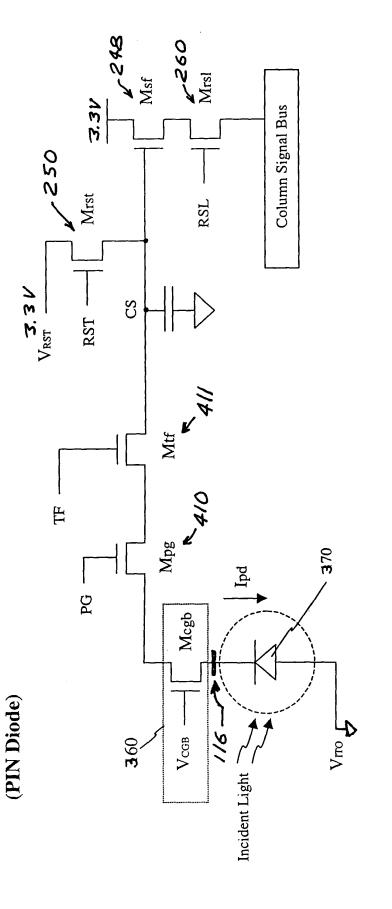


F1G.9



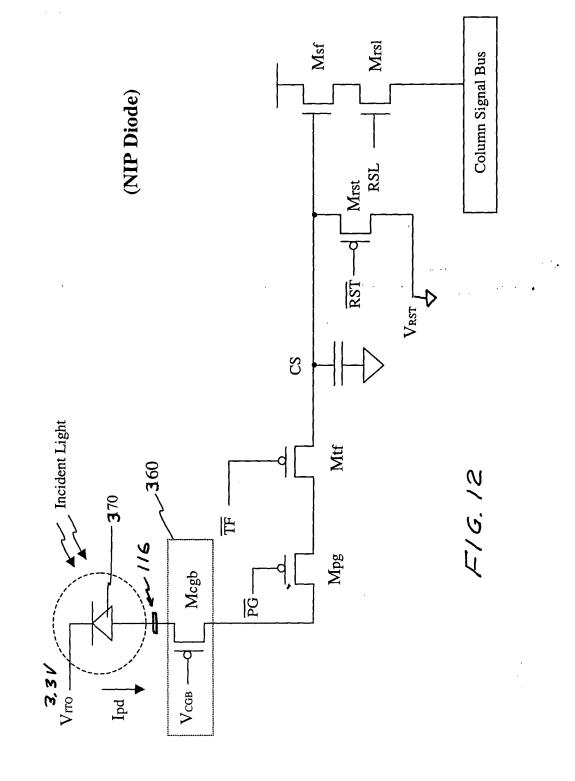
F/G. 10

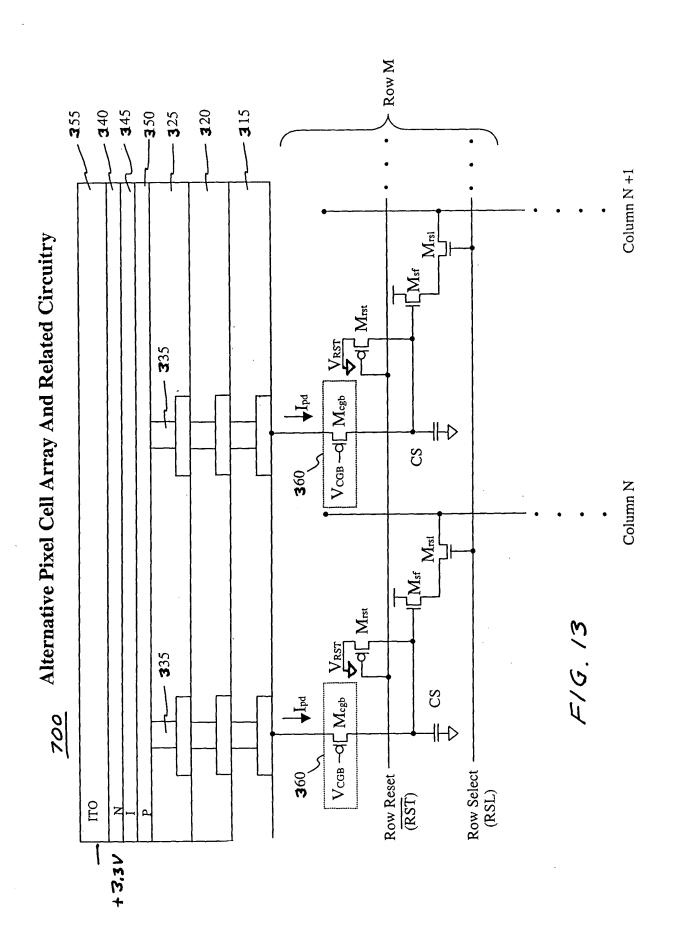
Individual Pixel Cell Circuitry (Six-Transistor Architecture)



F16. 11

Individual Pixel Cell Circuitry (Six-Transistor Architecture)





F1G. 14

# **PBIN Pixel Architecture**

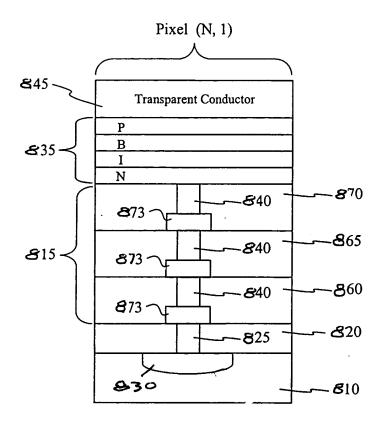
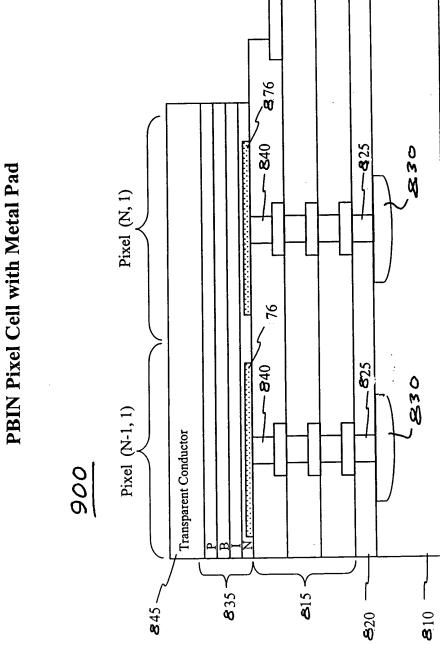
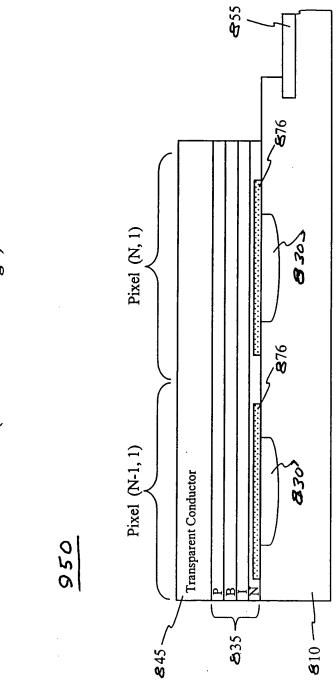


FIG. 15



855

PBIN Pixel Cell with Metal Pad (Alternative Design)



# POAP Sensor Utilizing Isolated Circuitry Region

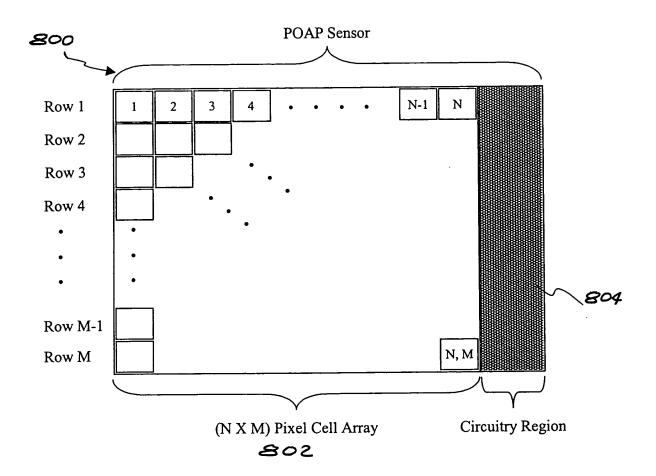


FIG. 17A

# **POAP Sensor Utilizing Multiple Circuitry Regions**

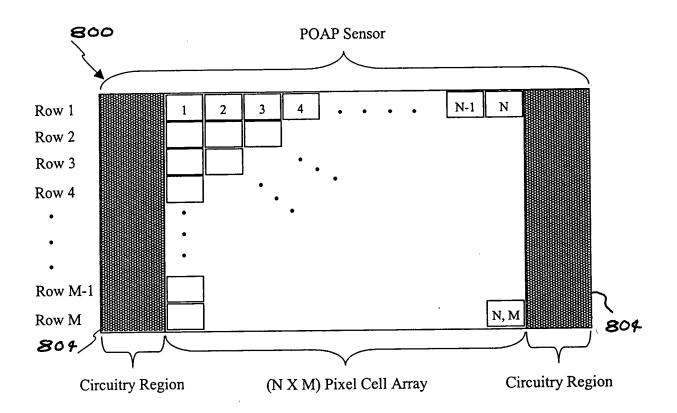
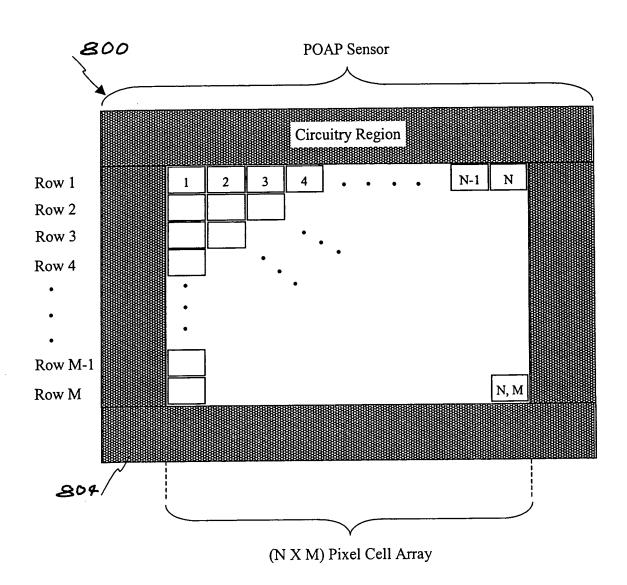
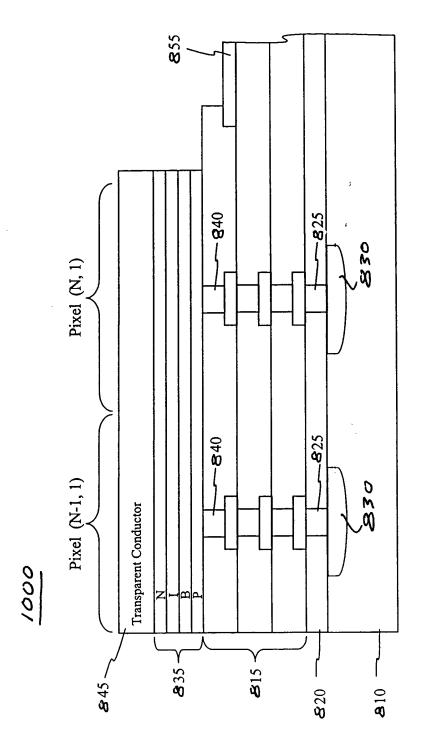


FIG. 17B

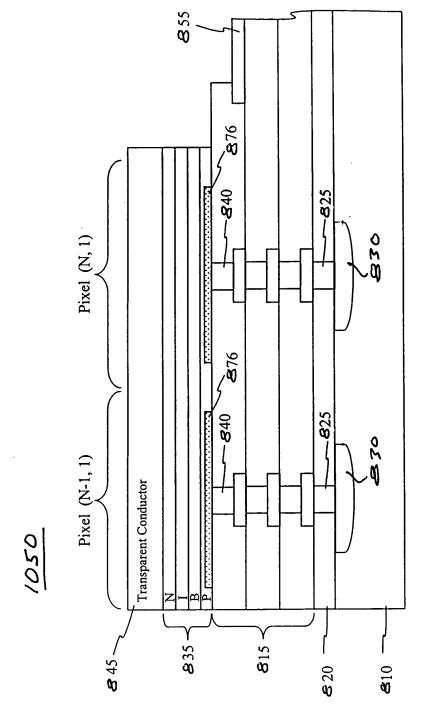
# **POAP Sensor Utilizing Four-Sided Circuitry Region**



F1G. 17C



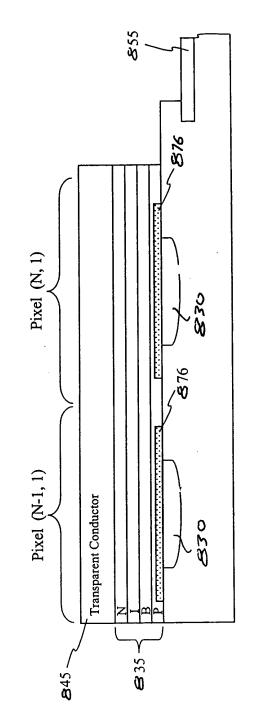
F16. 18A



F16, 18B

NIBP Pixel Cell with Metal Pad (Alternative Design)

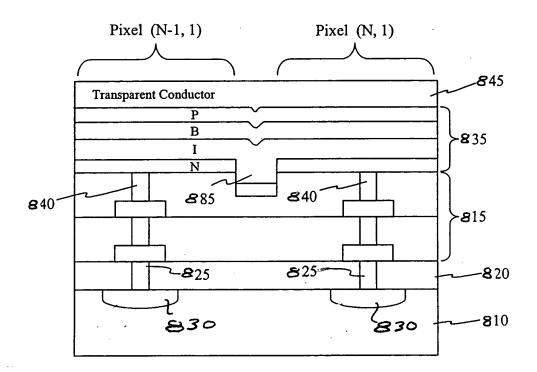
1100



F16 18C

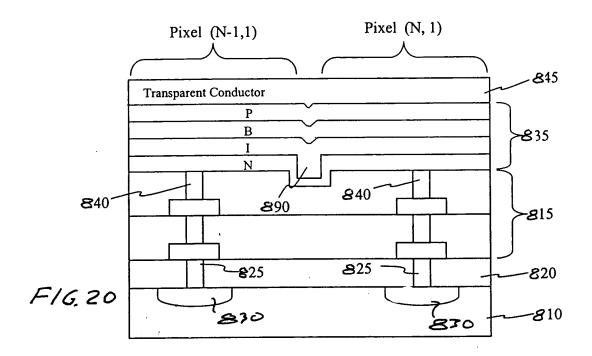
# **POAP Sensor Having A Discontinuous Trench**

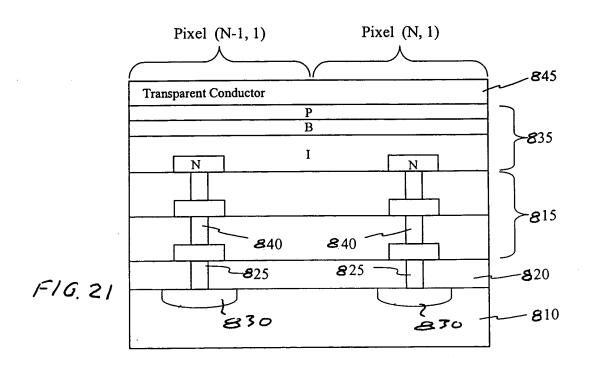
# 1150

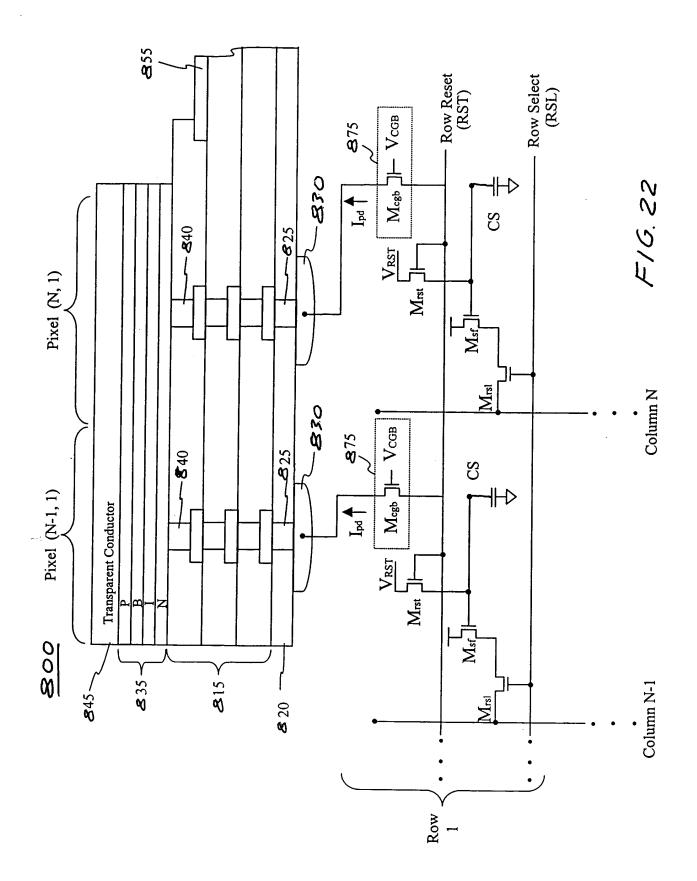


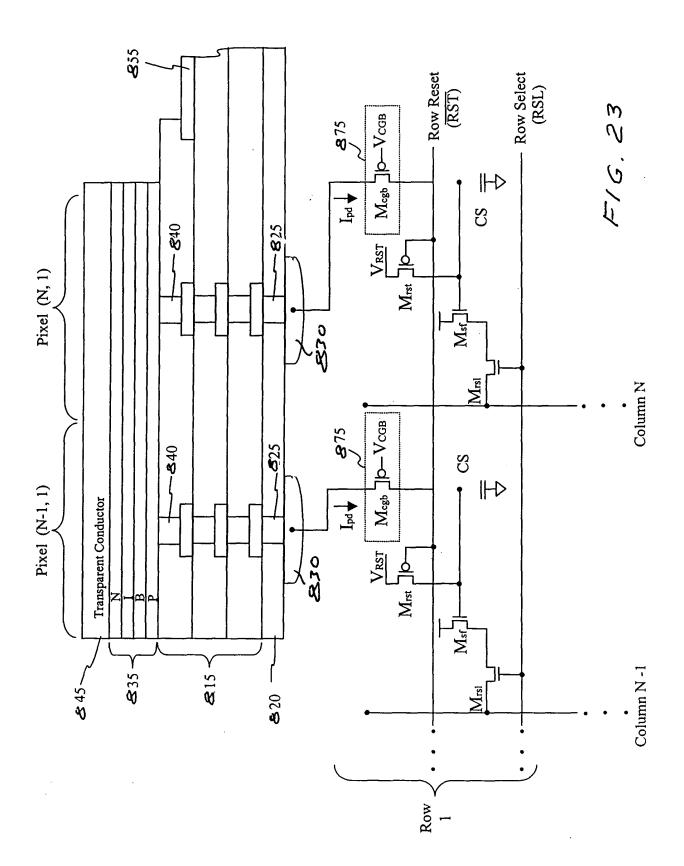
F1G. 19

# **POAP Sensors Having Trench And Patterned Bottom Layers**

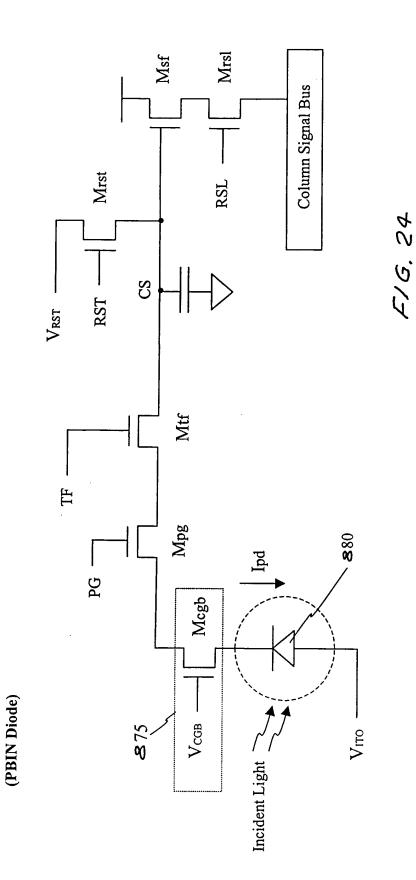




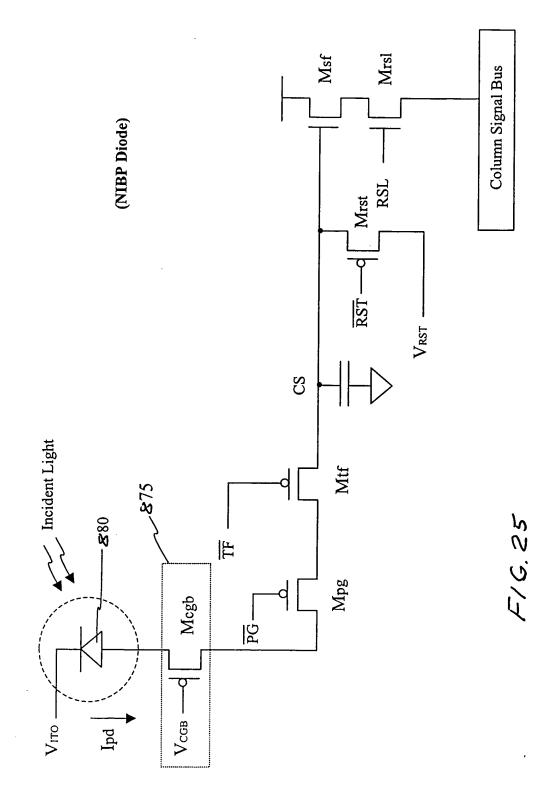




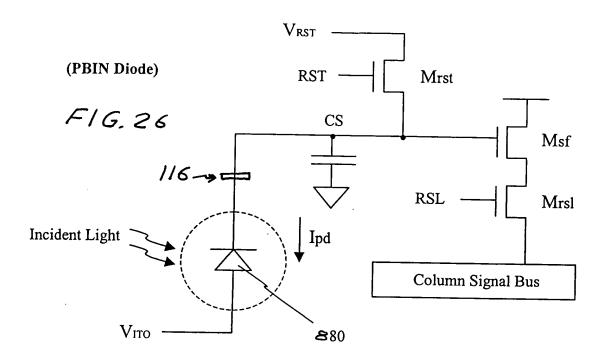
# Individual Pixel Cell Circuitry (Six-Transistor Architecture)

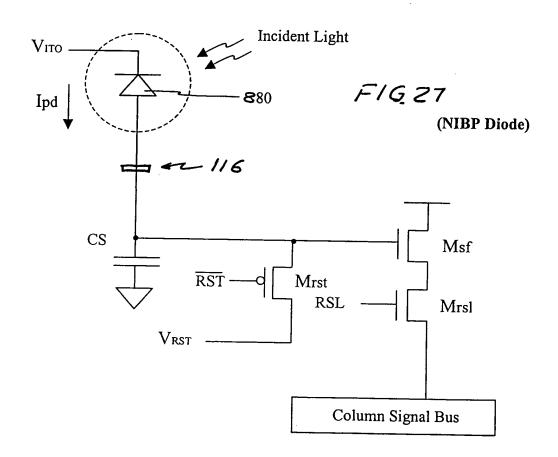


Individual Pixel Cell Circuitry (Six-Transistor Architecture)



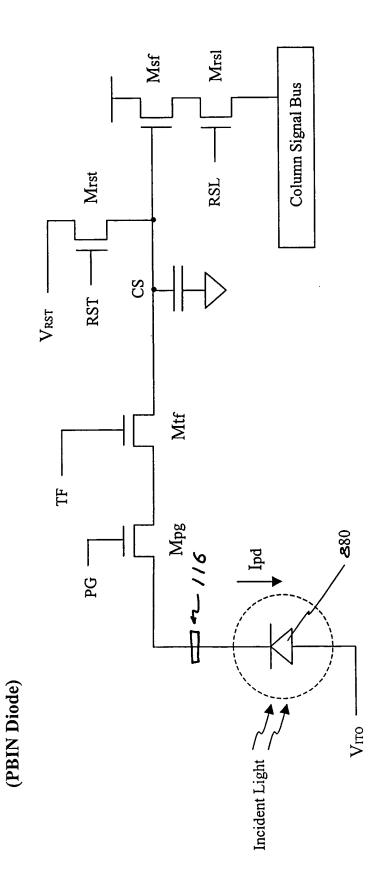
# Individual Pixel Cell Circuitry Without GBT





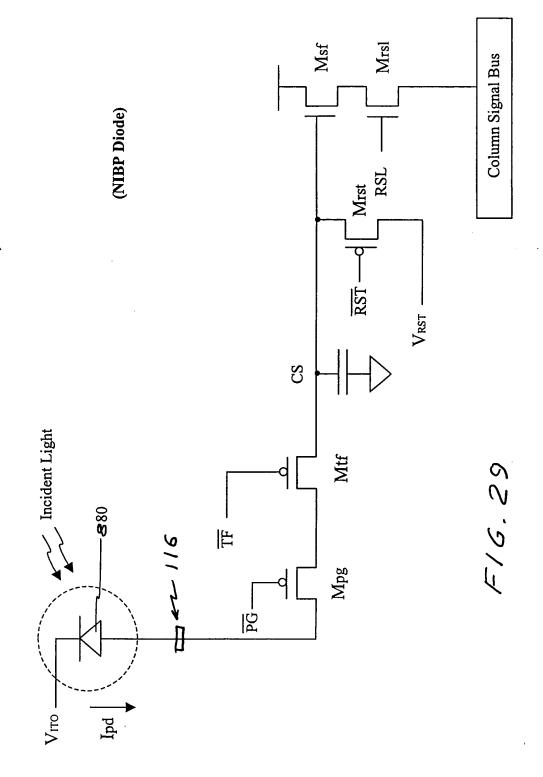
# Individual Pixel Cell Circuitry Without GBT (Five-Transistor Architecture)

# (Five-Tr

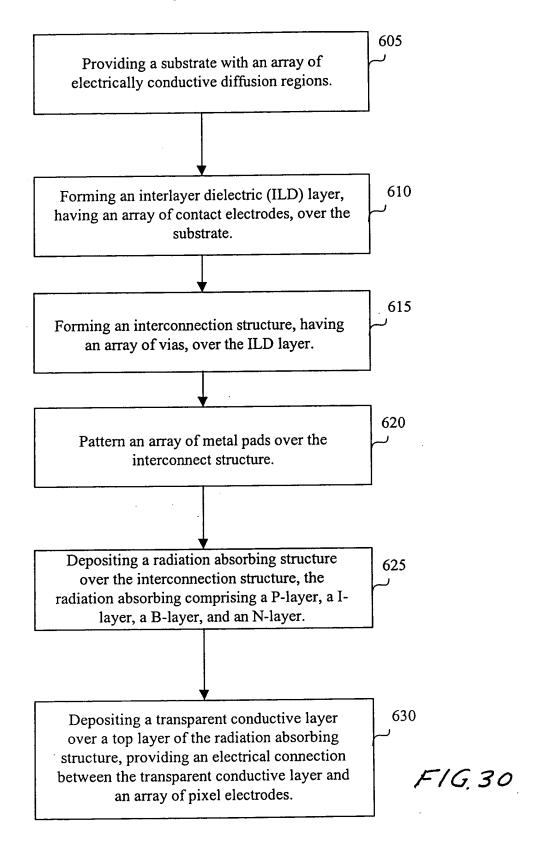


F16.28

# Individual Pixel Cell Circuitry Without GBT (Five-Transistor Architecture)



# Fabricating A POAP Sensor



## **POAP Sensor Fabrication**

